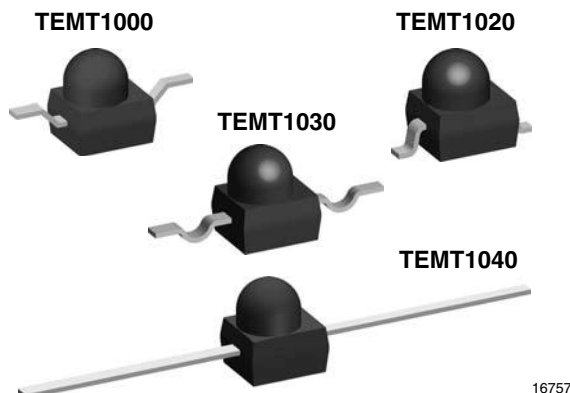


Silicon NPN Phototransistor, RoHS Compliant



FEATURES

- Package type: surface mount
- Package form: GW, RGW, yoke, axial
- Dimensions (L x W x H in mm): 2.5 x 2 x 2.7
- High radiant sensitivity
- Daylight blocking filter matched with 870 nm to 950 nm IR emitters
- Fast response times
- Angle of half sensitivity: $\phi = \pm 15^\circ$
- Package matches with IR emitter series TSML1000
- Floor life: 168 h, MSL 3, acc. J-STD-020
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC



RoHS
COMPLIANT

DESCRIPTION

TEMT1000 series are silicon NPN phototransistors with high radiant sensitivity in black, surface mount, plastic packages with lens and daylight blocking filter. Filter bandwidth is matched with 870 nm to 950 nm IR emitters.

APPLICATIONS

- Detector in electronic control and drive circuits
- IR detector for daylight application
- Photo interrupters
- Counter
- Encoder

PRODUCT SUMMARY

COMPONENT	I_{ca} (mA)	ϕ (deg)	$\lambda_{0.5}$ (nm)
TEMT1000	7	± 15	730 to 1000
TEMT1020	7	± 15	730 to 1000
TEMT1030	7	± 15	730 to 1000
TEMT1040	7	± 15	730 to 1000

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TEMT1000	Tape and reel	MOQ: 1000 pcs, 1000 pcs/reel	Reverse gullwing
TEMT1020	Tape and reel	MOQ: 1000 pcs, 1000 pcs/reel	Gullwing
TEMT1030	Tape and reel	MOQ: 1000 pcs, 1000 pcs/reel	Yoke
TEMT1040	Bulk	MOQ: 1000 pcs, 1000 pcs/bulk	Axial leads

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Emitter collector voltage		V_{ECO}	5	V
Collector current		I_C	50	mA
Collector peak current	$t_p/T = 0.5, t_p \leq 10$ ms	I_{CM}	100	mA
Power dissipation	$T_{amb} \leq 55^\circ\text{C}$	P_V	100	mW
Junction temperature		T_j	100	$^\circ\text{C}$
Operating temperature range		T_{amb}	- 40 to + 85	$^\circ\text{C}$
Storage temperature range		T_{stg}	- 40 to + 100	$^\circ\text{C}$
Soldering temperature	$t \leq 5$ s	T_{sd}	260	$^\circ\text{C}$
Thermal resistance junction/ambient	Soldered on PCB with pad dimensions: 4 mm x 4 mm	R_{thJA}	400	K/W

Note

$T_{amb} = 25^\circ\text{C}$, unless otherwise specified



TEMT1000, TEMT1020, TEMT1030, TEMT1040

Silicon NPN Phototransistor, RoHS Compliant Vishay Semiconductors

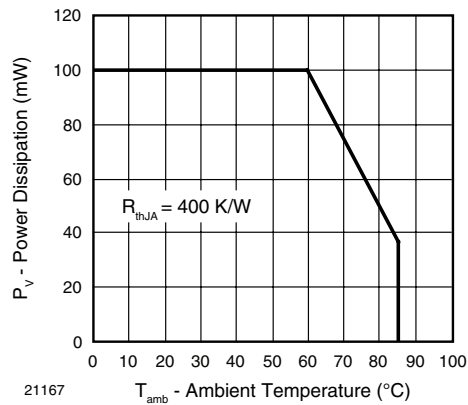


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector emitter voltage	$I_C = 1 \text{ mA}$	V_{CEO}	70			V
Collector emitter dark current	$V_{CE} = 20 \text{ V}, E = 0$	I_{CEO}		1	200	nA
Collector emitter capacitance	$V_{CE} = 5 \text{ V}, f = 1 \text{ MHz}, E = 0$	C_{CEO}		3		pF
Angle of half sensitivity		ϕ		± 15		deg
Wavelength of peak sensitivity		λ_p		880		nm
Range of spectral bandwidth		$\lambda_{0.5}$		730 to 1000		nm
Collector emitter saturation voltage	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, I_C = 0.1 \text{ mA}$	V_{CEsat}			0.3	V
Turn-on time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$	t_{on}		2.0		μs
Turn-off time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$	t_{off}		2.3		μs
Cut-off frequency	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$	f_c		180		kHz
Collector light current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, V_{CE} = 5 \text{ V}$	I_{ca}	2	7.0		mA

Note

$T_{amb} = 25^\circ\text{C}$, unless otherwise specified

BASIC CHARACTERISTICS

$T_{amb} = 25^\circ\text{C}$, unless otherwise specified

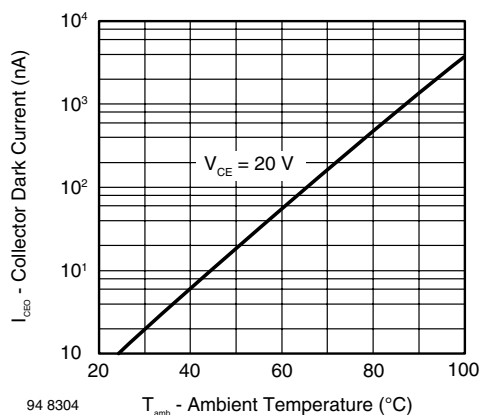


Fig. 2 - Collector Dark Current vs. Ambient Temperature

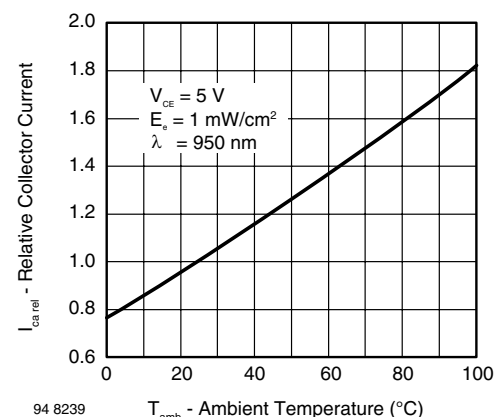


Fig. 3 - Relative Collector Current vs. Ambient Temperature

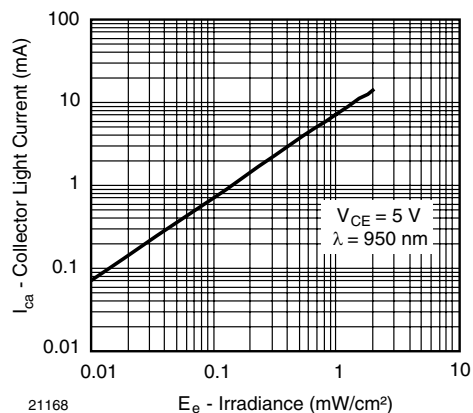


Fig. 4 - Collector Light Current vs. Irradiance

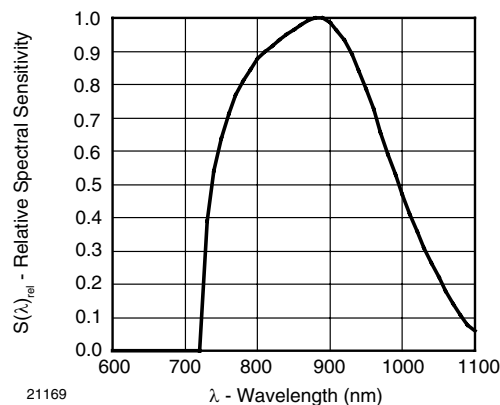


Fig. 7 - Relative Spectral Sensitivity vs. Wavelength

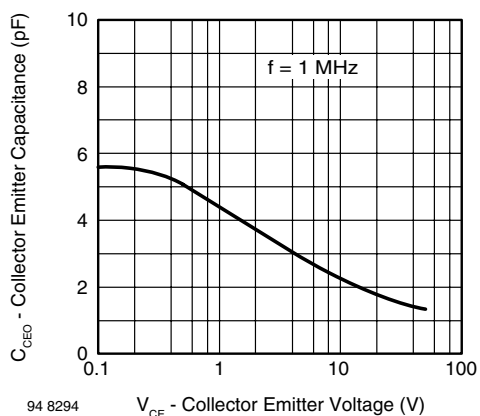


Fig. 5 - Collector Emitter Capacitance vs. Collector Emitter Voltage

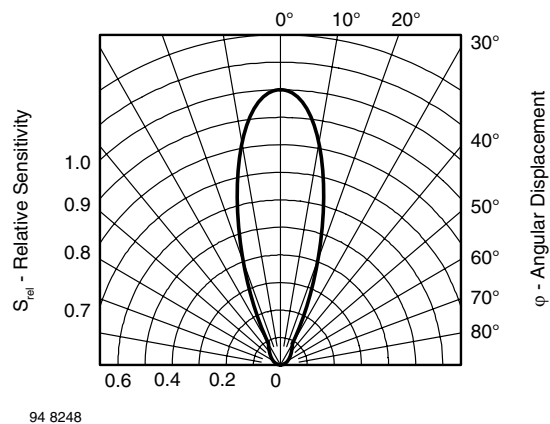


Fig. 8 - Relative Radiant Sensitivity vs. Angular Displacement

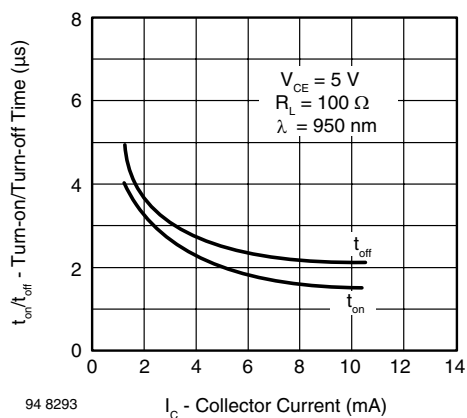


Fig. 6 - Turn-on/Turn-off Time vs. Collector Current



TEMT1000, TEMT1020, TEMT1030, TEMT1040

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PRECAUTIONS FOR USE

1. Over-current-proof

Customer must apply resistors for protection, otherwise slight voltage shift will cause big current change (burn out will happen).

2. Storage

2.1 Storage temperature and rel. humidity conditions are: 5 °C to 35 °C, R.H. 60 %.

2.2 Floor life must not exceed 168 h, acc. to JEDEC level 3, J-STD-020.

Once the package is opened, the products should be used within a week. Otherwise, they should be kept in a damp proof box with desiccant.

Considering tape life, we suggest to use products within one year from production date.

2.3 If opened more than one week in an atmosphere 5 °C to 35 °C, R.H. 60 %, devices should be treated at 60 °C $\pm$ 5 °C for 15 h.

2.4 If humidity indicator in the package shows pink color (normal blue), then devices should be treated with the same conditions as 2.3.

REFLOW SOLDER PROFILE

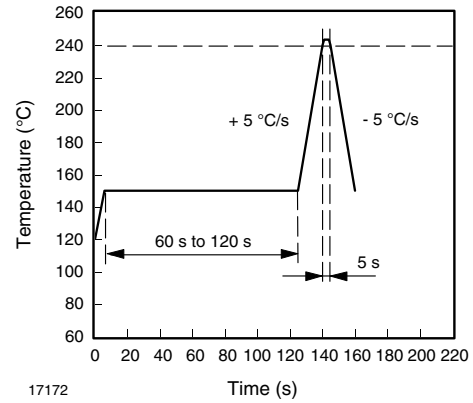
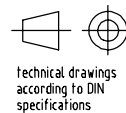
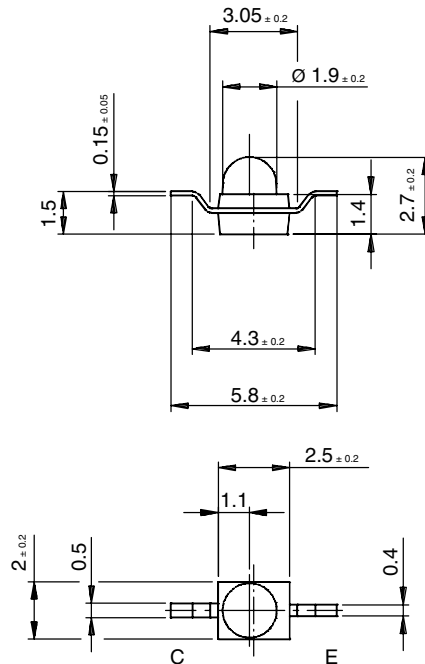
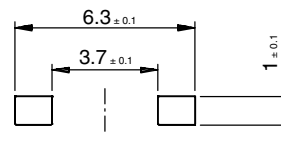


Fig. 9 - Lead Tin (SnPb) Reflow Solder Profile

PACKAGE DIMENSIONS in millimeters: TEMT1000



Solder pad proposal



Drawing-No.: 6.544-5326.01-4

Issue: 4; 02.04.03

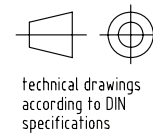
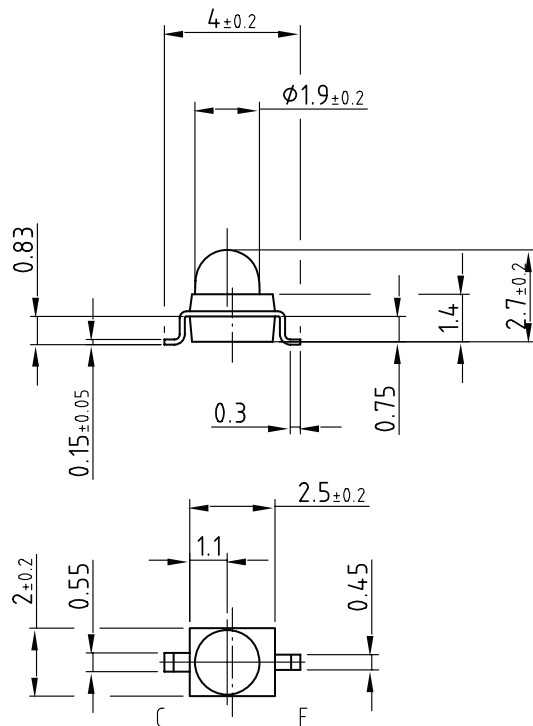
16104

TEMT1000, TEMT1020, TEMT1030, TEMT1040

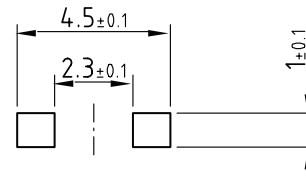
Vishay Semiconductors Silicon NPN Phototransistor, RoHS Compliant



PACKAGE DIMENSIONS in millimeters: TEMT1020



Solder pad proposal

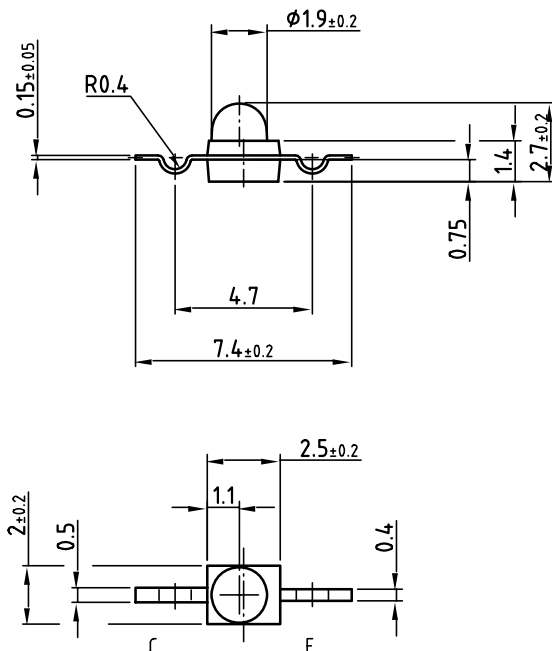


Drawing-No.: 6.544-5325.01-4

Issue: 5; 19.01.06

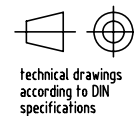
16105

PACKAGE DIMENSIONS in millimeters: TEMT1030



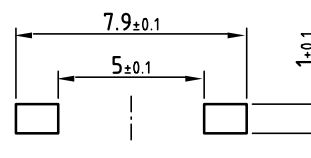
Drawing-No.: 6.544-5329.02-4

Issue: 3; 08.05.03



All dimensions in mm

Solder pad proposal



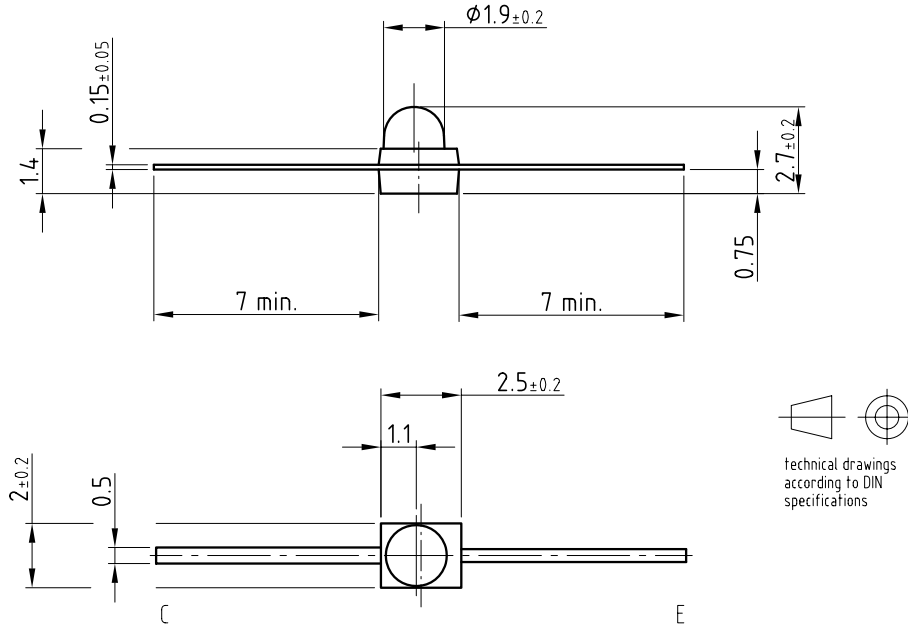
16756



TEMT1000, TEMT1020, TEMT1030, TEMT1040

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PACKAGE DIMENSIONS in millimeters: TEMT1040

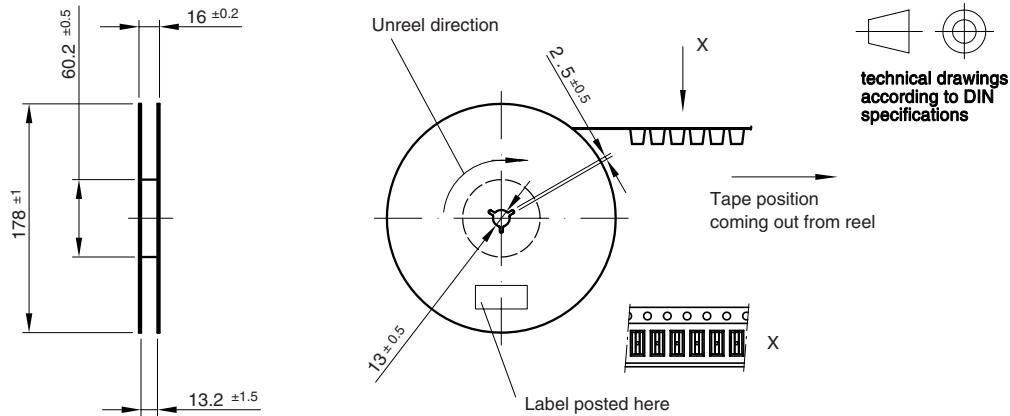


Drawing-No.: 6.544-5339.01-4

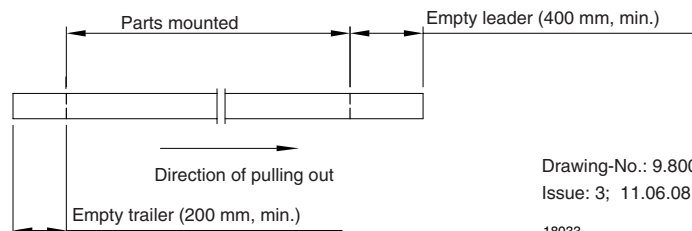
Issue: 2; 02.04.03

16500

REEL DIMENSIONS in millimeters



Leader and trailer tape:



Drawing-No.: 9.800-5080.01-4

Issue: 3; 11.06.08

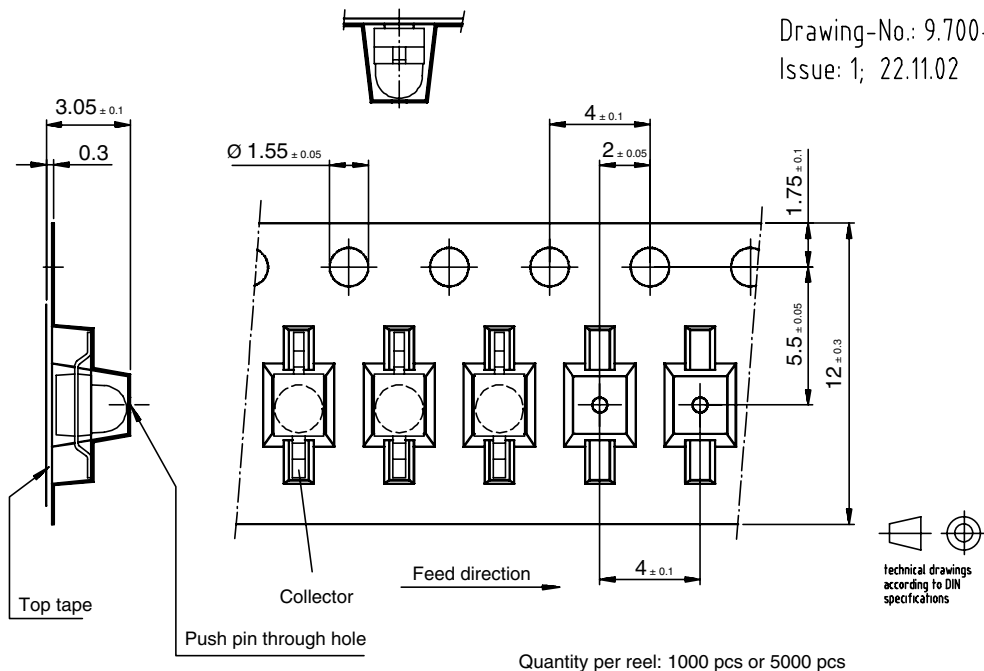
18033

TEMT1000, TEMT1020, TEMT1030, TEMT1040

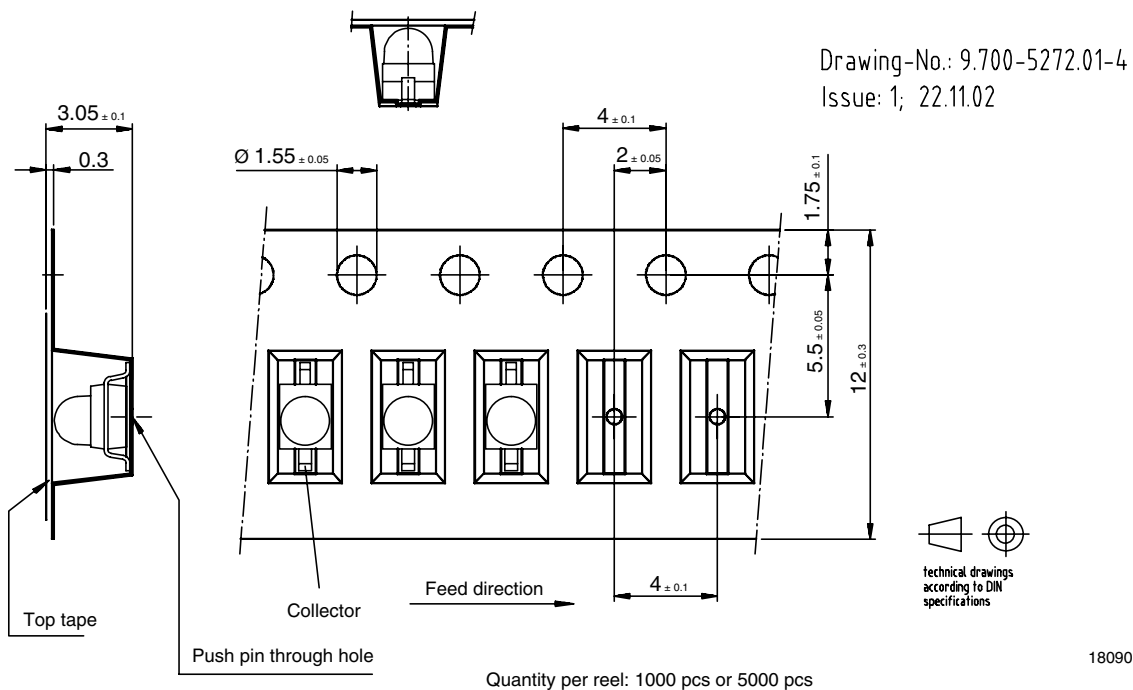
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TAPING DIMENSIONS in millimeters: TEMT1000



TAPING DIMENSIONS in millimeters: TEMT1020

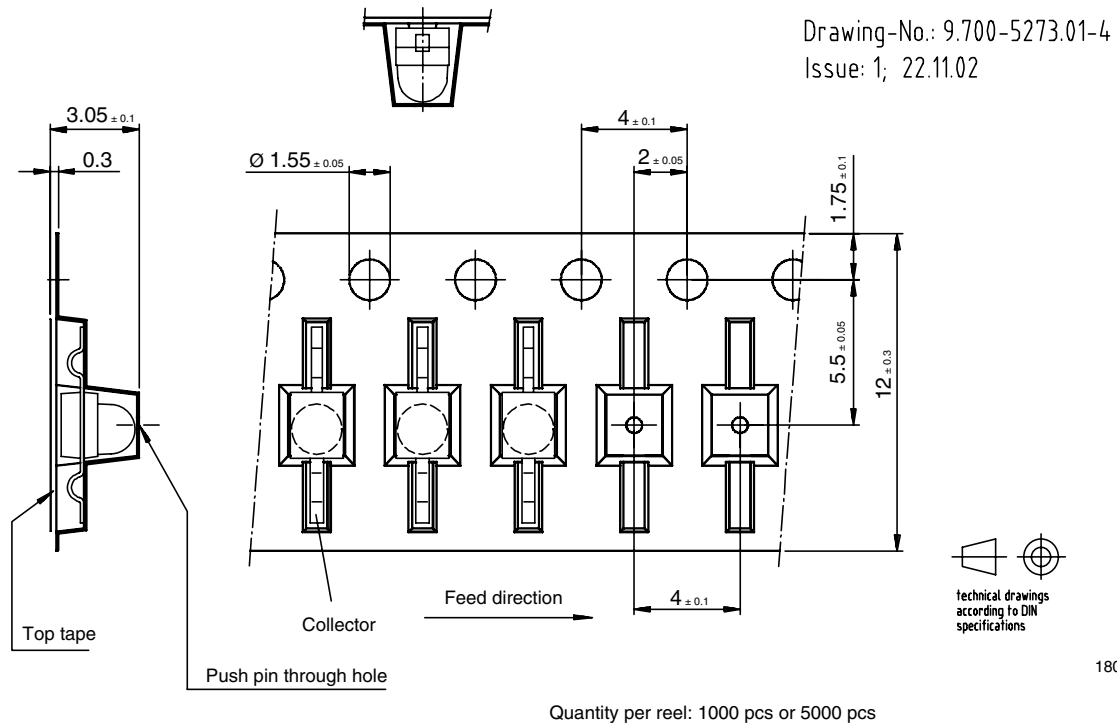




TEMT1000, TEMT1020, TEMT1030, TEMT1040

Silicon NPN Phototransistor, RoHS Compliant Vishay Semiconductors

TAPING DIMENSIONS in millimeters: **TEMT1030**



18091



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